

SPECIFICATION OF LED CHIP

C1200-35

[NIR]

1) Commodity Type and Physical Characteristics.

1. Material InGaAsP/InP(DDH)
2. Electrode Top Side P (anode) side : Au Alloy
Bottom Side N (cathode) side : Au Alloy
3. Electrode Pattern Fig.1
4. Chip Size Fig.2
5. Chip Thickness Fig.2
6. Emission Area Fig.2

2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	V _f	I _f =20mA		0.8	1.3	V
Reverse Current	I _r	V _r =3V			10	uA
Power Intensity	P _o	I _f =20mA		0.6		mW
Peak Wavelength	λ _P	I _f =20mA		1200		nm
Spectral Radiation Bandwidth	Δλ	I _f =20mA		100		nm
RiseTime	t _r	I _f =20mA		10		ns
FallTime	t _f	I _f =20mA		10		ns

‡ Die shall be mounted on TO=18 gold header without resin coated. (Ta=25°C)

[Unit: μm]

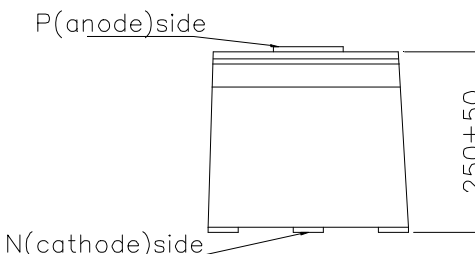
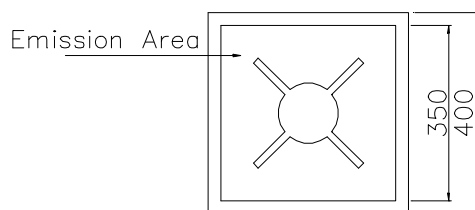
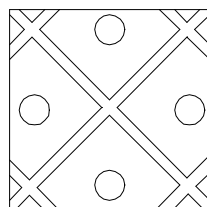
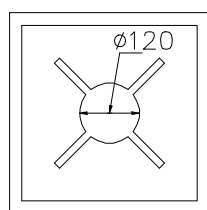


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area